SERIAL NO. ATTY DOCKET NO. NEC-WNZ-09/612,551 APPLICANT(S) INFORMATION DISCLOSURE CITATION TANABE et al (Use several sheets if necessary) FILING DATE GROUP 700 7/7/2000 **U.S. PATENT DOCUMENTS** *EXAMINER FILING DATE CLASS SUBCLASS DOCUMENT NUMBER DATE NAME INITIAL IF APPROPRIATE OIP OCT 1 0 2000 RADEMARY

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
	DOGGINETT WORLDER		000111111	05.00	00001100	YES	NO
GSE	7-118443	12/18/95	JAPAN	H01L	21/20		>
GSE	5-211167	8/20/93	JAPAN	HO1L	21/336	<	
69E	5-909191	4/9/93	JAPAN	HO1L	21/268	\	
GSE	5-182923	7/23/93	JAPAN	HO1L	21/268	18	
65P	7-99321	4/11/95	JAPAN	HO1L	29/186	S E	, ,

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

Crystalline Si Films for Integrated Actrive-Matrix Liquid-Crstal Displays, James S. Im and Robert S. Sposili, Mrs Bulletin, March 1996, pages 39-48.

Segmential Letters Solidification of Thir Silican Films on SiO2 Debut S. Sociii and James S. Lee, April Phys. Lett. (0.430)

Sequential Lateral Solidification of Thin Silicon Films on SiO2, Robert S. Sposili and James S. Im, Appl. Phys. Lett. 69 (19), 4 November 1996, pages 2864-2866

EXAMINER Hollow & Frank Date considered 18,2001

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

ATTY DOCKET NO. SERIAL NO. NEC-WNZ-09/612,551 INFORMATION DISCLOSURE CITATION APPLICANT(S) TANABE et al (Use several sheets if necessary) FILING DATE GROUP 7/7/2000 **U.S. PATENT DOCUMENTS** *EXAMINER FILING DATE CLASS DOCUMENT NUMBER DATE NAME SUBCLASS INITIAL IF APPROPRIATE **FOREIGN PATENT DOCUMENTS** TRANSLATION DOCUMENT NUMBER DATE COUNTRY CLASS SUBCLASS YES NO 9-7911 1/10/97 **JAPAN** HO1L 21/02 1/17/97 9-17729 **JAPAN** HO1L 21/20 9-148246 6/6/97 **JAPAN** HO1L 21/20 10-116989 5/6/98 **JAPAN** HO1L 29/786 10-149984 6/2/98 **JAPAN** HO1L 21/20 OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) Single-crystal Si Films for Thin-Film transistor Devices, James S. Im, Robert S. Sposili, and M.A. Crowder, Appl. Phys. Lett. 70 (25), 23 June 1997, American Institute of Physics, page 3434-3436.

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

EXAMINER

Effects of Light Pulse Duratio on Excimer-Laser Crystallization Characteristics of Silicon Thin Films, Ishihara, Yeh, Hattori and Matsumura, Jpn. J. Appl. Phys. Vol. 34 (1995) pp. 1759-1764, Page 1, No. 4A, April 1995

DATE CONSIDERED

ATTY DOCKET NO. SERIAL NO. NEC-WNZ-09/612,551 APPLICANT(S) INFORMATION DISCLOSURE CITATION TANABE et al (Use several sheets if necessary) GROUP FILING DATE 7/7/2000 **U.S. PATENT DOCUMENTS** *EXAMINER FILING DATE CLASS SUBCLASS DOCUMENT NUMBER DATE NAME INITIAL IF APPROPRIATE

					İ					
			THADEMARK SHOW				-			
•	FOREIGN PATENT DOCUMENTS									
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO				
65E	11-17185	1/22/99	JAPAN	HO1L	29/786	123	NO			
6SE	5-21393	1/29/93	JAPAN	HO1L	21/302	J				
							l			

OCT 1 0 2000

Improvement of structural and electrical properties in low-temperature gate oxides for poly-Si TFTs by controlling O2/SiH4 ratios, Yuda, Tanabe and Okumura, AM-LCD 97, The Japan Society of Applied Physics, Digest of Technical Papers, 1997, International Workshop on Active-Matrix Liquid-Crystal Displays - TFT Technologies and Related Materials. September 11-12, 1997, Kogakuin University, Tokyo, Japan, pages 87-89

Excimer Laser Crystallization of Amorphous Silicon Films, Tanabe, Sera, Nakamura, Hirata, Yuda and Okumura, reprinted from the NEC Research & Development, Vo. 35, No. 3, pp. 254-260, July 1994

(Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER Sexpasses & Every Date considered 18, 2001

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

P09C/REV03

OTHER DOCUMENTS

70

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

ATTY DOCKET NO.	SERIAL NO.
NEC-WNZ-	09/612,551
APPLICANT(S)	
TANABE et al	

(out develui anotis ii necessary)					FILING DATE GROUP 700				
	·· — ·-		U.S	S. PATENT	DOCUMENTS				
*EXAMINER	DOCUMENT NUMBER DATE		DATE		NAME .	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
								-	
					0126				
			4,		OCT 1 0 2000 CS				
					PADTUS BY CHE				
					O DA				
					-				
			FORE	IGN PATE	ENT DOCUMENTS				
		DOCUMENT NUMBER	DATE		COUNTRY	CLASS	SUBCLASS		LATION
							-	YES	NO
							1		
	+		-		area .		 		
				<u> </u>			 		
	-						+		
<u> </u>		OTHER DOCUME	NTS (Includin		- Title Data Dortinget	Darra Eta	TECHNOL		
	\neg	OTHER DOCUME	and Liquids, Ro	bert C. R	r, Title, Date, Pertinent eid, John M. Prausnitz, Br	Pages, ⊑ιс. uce E. Poling	, Fourth Editio	n, Cover/(Contents
GSE	Page, Appendix B, page 734, and Index page.								
GGE	Transport Phenomena, Department of Chemical Engineering, Univesity of Wisconsin, Madison Wisconsin, Preface, pages 508-513, Table B-2, and Appendix C (page 747).								
EXAMINER	eoffe				DATE CONSIDERED				
*EXAMINER:	: Initial if re	1	r or not citation is i	in conform	ance with MPEP 609; Draw I				and not

Form PTO-A820 (also form PTO-1449)

Copyright 1994 LegalStar

P09C/REV03

Patent and Trademark Office * U.S. DEPARTMENT OF COMMERCE

1